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Journal of Vacuum Science & Technology A (ISSN: 0734-2101) is published six times annually (Jan/Feb, Mar/Apr, May/Jun, Jul/Aug, Sep/Oct, Nov/Dec) by AVS through the American Institute of Physics, Suite 1N01, 2 Huntington Quadrangle, Melville, NY 11747-4502. 2010 subscription rates are: US\$1520. POSTMASTER: Send address changes to *Journal of Vacuum Science & Technology A*, Membership Services, AVS, 125 Maiden Lane, 15th Floor, New York, NY 10038, membership@avs.org, www.avs.org. Periodicals postage paid at Huntington Station, NY 11746, and at additional mailing offices.

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